

# LC<sup>2</sup>MOS Precision Mini-DIP Analog Switch

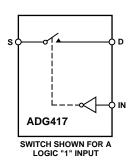
**ADG417** 

#### **FEATURES**

44 V Supply Maximum Ratings  $V_{SS}$  to  $V_{DD}$  Analog Signal Range Low On Resistance (<35  $\Omega$ ) Ultralow Power Dissipation (<35  $\mu$ W) Fast Switching Times  $t_{ON}$  (160 ns max)  $t_{OFF}$  (100 ns max) Break-Before-Make Switching Action Plug-In Replacement for DG417

APPLICATIONS
Precision Test Equipment
Precision Instrumentation
Battery Powered Systems
Sample Hold Systems

### FUNCTIONAL BLOCK DIAGRAM



### GENERAL DESCRIPTION

The ADG417 is a monolithic CMOS SPST switch. This switch is designed on an enhanced LC<sup>2</sup>MOS process that provides low power dissipation yet gives high switching speed, low on resistance and low leakage currents.

The on resistance profile of the ADG417 is very flat over the full analog input range ensuring excellent linearity and low distortion. The part also exhibits high switching speed and high signal bandwidth. CMOS construction ensures ultralow power dissipation making the parts ideally suited for portable and battery powered instruments.

The ADG417 switch, which is turned ON with a logic low on the control input, conducts equally well in both directions when ON and has an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. The ADG417 exhibits break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital input.

### PRODUCT HIGHLIGHTS

- Extended Signal Range
   The ADG417 is fabricated on an enhanced LC<sup>2</sup>MOS process, giving an increased signal range that extends to the supply rails
- 2. Ultralow Power Dissipation
- 3. Low Ron
- 4. Single Supply Operation
  For applications where the analog signal is unipolar, the ADG417 can be operated from a single rail power supply.
  The part is fully specified with a single +12 V power supply and will remain functional with single supplies as low as +5 V.

### REV. A

## ADG417\* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

## COMPARABLE PARTS 🖳

View a parametric search of comparable parts.

## **DOCUMENTATION**

### **Application Notes**

 AN-1313: Configuring the AD5422 to Combine Output Current and Output Voltage to a Single Output Pin

### **Data Sheet**

 ADG417: LC<sup>2</sup>MOS Precision Mini-DIP Analog Switch Data Sheet

### REFERENCE MATERIALS 🖵

### **Product Selection Guide**

• Switches and Multiplexers Product Selection Guide

### **Technical Articles**

- CMOS Switches Offer High Performance in Low Power, Wideband Applications
- Data-acquisition system uses fault protection
- Enhanced Multiplexing for MEMS Optical Cross Connects
- · Temperature monitor measures three thermal zones

## DESIGN RESOURCES 🖵

- ADG417 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- Symbols and Footprints

## **DISCUSSIONS**

View all ADG417 EngineerZone Discussions.

### SAMPLE AND BUY 🖵

Visit the product page to see pricing options.

## **TECHNICAL SUPPORT**

Submit a technical question or find your regional support number.

### DOCUMENT FEEDBACK 🖳

Submit feedback for this data sheet.

# **ADG417—SPECIFICATIONS**

 $\textbf{Dual Supply}^{1} \ \, (\textbf{V}_{DD} = +15 \ \textbf{V} \ \pm \ 10\%, \ \textbf{V}_{SS} = -15 \ \textbf{V} \ \pm \ 10\%, \ \textbf{V}_{L} = +5 \ \textbf{V} \ \pm \ 10\%, \ \textbf{GND} = 0 \ \textbf{V}, \ \textbf{unless otherwise noted})$ 

	B Version -40°C to		T Version -55°C to			
Parameter	+25°C	+85°C	+25°C	+125°C	Units	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range		$V_{SS}$ to $V_{DD}$		$V_{SS}$ to $V_{DD}$	V	
$R_{ON}$	25		25		$\Omega$ typ	$V_D = \pm 12.5 \text{ V}, I_S = -10 \text{ mA}$
	35	45	35	45	$\Omega$ max	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
LEAKAGE CURRENTS						$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
Source OFF Leakage I <sub>S</sub> (OFF)	±0.1		$\pm 0.1$		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \mp 15.5 \text{ V};$
	±0.25	±5	±0.25	±15	nA max	Test Circuit 2
Drain OFF Leakage I <sub>D</sub> (OFF)	±0.1		$\pm 0.1$		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \mp 15.5 \text{ V};$
	±0.25	±5	±0.25	±15	nA max	Test Circuit 2
Channel ON Leakage ID, IS (ON)	±0.1		$\pm 0.1$		nA typ	$V_S = V_D = \pm 15.5 \text{ V};$
<i>3 B, 3</i> (	±0.4	±5	$\pm 0.4$	±30	nA max	Test Circuit 3
DIGITAL INPUTS						
Input High Voltage, V <sub>INH</sub>		2.4		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8		0.8	V max	
Input Current						
I <sub>INL</sub> or I <sub>INH</sub>		±0.005		$\pm 0.005$	μA typ	$V_{IN} = V_{INI, or V_{INH}}$
		±0.5		±0.5	μA max	
DYNAMIC CHARACTERISTICS <sup>2</sup>						
t <sub>ON</sub>	100		100		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
	160	200	145	200	ns max	$V_S = \pm 10 \text{ V}$ ; Test Circuit 4
$t_{ m OFF}$	60		60		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
	100	150	100	150	ns max	$V_S = \pm 10 \text{ V}$ ; Test Circuit 4
Charge Injection	7		7		pC typ	$V_S = 0 V, R_L = 0 \Omega,$
						$C_L = 10 \text{ nF}$ ; Test Circuit 5
OFF Isolation	80		80		dB typ	$R_L = 50 \Omega$ , $f = 1 MHz$ ;
						Test Circuit 6
$C_S$ (OFF)	6		6		pF typ	
$C_D$ (OFF)	6		6		pF typ	
$C_D, C_S (ON)$	55		55		pF typ	
POWER REQUIREMENTS						$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
${ m I}_{ m DD}$	0.0001		0.0001		μA typ	$V_{IN} = 0 \text{ V or } 5 \text{ V}$
	1	2.5	1	2.5	μA max	
$I_{SS}$	0.0001		0.0001		μA typ	
	1	2.5	1	2.5	μA max	
${ m I_L}$	0.0001		0.0001		μA typ	$V_{L} = +5.5 \text{ V}$
	1	2.5	1	2.5	μA max	

### NOTES

Specifications subject to change without notice.

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 $<sup>^1</sup>Temperature$  ranges are as follows: B Version: –40  $^{\circ}C$  to +85  $^{\circ}C;$  T Version: –55  $^{\circ}C$  to +125  $^{\circ}C.$ 

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

# Single Supply $^{1}$ (VDD = +12 V $\pm$ 10%, VSS = 0 V, VL = +5 V $\pm$ 10%, GND = 0 V, unless otherwise noted)

	B Version -40°C to		T Version -55°C to			
Parameter	+25°C	+85°C	+25°C	+125°C	Units	Test Conditions/Comments
ANALOG SWITCH Analog Signal Range R <sub>ON</sub>	40	0 to $V_{DD}$	40	0 to $V_{DD}$	V Ω typ	$V_D = +3 \text{ V}, +8.5 \text{ V}, I_S = -10 \text{ mA}$
		60		70	Ω max	$V_{\rm DD} = +10.8 \text{ V}$
LEAKAGE CURRENT						V <sub>DD</sub> = +13.2 V
Source OFF Leakage I <sub>S</sub> (OFF)	±0.1 ±0.25	±5	±0.1 ±0.25	±15	nA typ nA max	$V_D = 12.2 \text{ V/1 V}, V_S = 1 \text{ V/12.2 V};$ Test Circuit 2
Drain OFF Leakage $I_D$ (OFF)	±0.1		±0.1		nA typ	$V_D = 12.2 \text{ V/1 V}, V_S = 1 \text{ V/12.2 V};$
Channel ON Leakage $I_D$ , $I_S$ (ON)	±0.25 ±0.1 ±0.4	±5 ±5	±0.25 ±0.1 ±0.4	±15 ±30	nA max nA typ nA max	Test Circuit 2 $V_S = V_D = 12.2 \text{ V/1 V};$ Test Circuit 3
DIGITAL INPUTS	20.1		20.1		III III III	rest direction
Input High Voltage, $V_{INH}$ Input Low Voltage, $V_{INL}$		2.4 0.8		2.4 0.8	V min V max	
Input Current		0.0		0.0	Villux	
I <sub>INL</sub> or I <sub>INH</sub>		±0.005 ±0.5		±0.005 ±0.5	μΑ typ μΑ max	$V_{IN} = V_{INL}$ or $V_{INH}$
DYNAMIC CHARACTERISTICS <sup>2</sup>						
$t_{ON}$	180	250	180	250	ns max	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = +8 V$ ; Test Circuit 4
$t_{ m OFF}$	85	110	85	110	ns max	$R_L = 300 \Omega$ , $C_L = 35 pF$ ; $V_S = +8 V$ ; Test Circuit 4
Charge Injection	11		11		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega,$ $C_L = 10 \text{ nF}; \text{ Test Circuit 5}$
OFF Isolation	80		80		dB typ	$R_L = 50 \Omega$ , $f = 1 MHz$ ; Test Circuit 6
C <sub>s</sub> (OFF)	13		13		pF typ	Test Shear 9
$C_D$ (OFF)	13		13		pF typ	
$C_D, C_S (ON)$	65		65		pF typ	
POWER REQUIREMENTS						$V_{\rm DD} = +13.2 \text{ V}$
$I_{\mathrm{DD}}$	0.0001		0.0001		μA typ	$V_{IN} = 0 \text{ V or } 5 \text{ V}$
T	1	2.5	1	2.5	μA max	V - 155V
$ m I_L$	0.0001	2.5	0.0001	2.5	μΑ typ μΑ max	$V_{L} = +5.5 \text{ V}$

### NOTES

Specifications subject to change without notice.

Table I. Truth Table

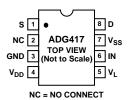
Logic	Switch Condition			
0	ON			
1	OFF			

### **ORDERING GUIDE**

Model	Temperature Range	Package Options*	
ADG417BN	-40°C to +85°C	N-8	
ADG417BR	-40°C to +85°C	SO-8	

<sup>\*</sup>N = Plastic DIP, SO = 0.15" Small Outline IC (SOIC).

# PIN CONFIGURATION DIP/SOIC



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¹Temperature ranges are as follows: B Version: −40 °C to +85 °C; T Version: −55 °C to +125 °C.

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

## **ADG417**

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Plastic P	Package, Power Dissipation	. 400 mW
$\theta_{JA}$ , T	hermal Impedance	100°C/W
Lead '	Temperature, Soldering (10 sec)	. +260°C
SOIC Pa	ackage, Power Dissipation	. 400 mW
$\theta_{JA}$ , T	hermal Impedance	155°C/W
Lead '	Temperature, Soldering	
Vap	or Phase (60 sec)	. +215°C
Infr	ared (15 sec)	. +220°C

#### NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

### CAUTION -

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG417 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



TERMINOLOGY	7	$V_{D}(V_{S})$	Analog voltage on terminals D, S.
$V_{\mathrm{DD}}$	Most positive power supply potential.	C <sub>S</sub> (OFF)	"OFF" switch source capacitance.
$V_{SS}$	Most negative power supply potential in dual	C <sub>D</sub> (OFF)	"OFF" switch drain capacitance.
	supplies. In single supply applications, it		"ON" switch capacitance.
$V_{I}$	may be connected to GND.  Logic power supply (+5 V).	t <sub>ON</sub>	Delay between applying the digital control
GND	Ground (0 V) reference.		input and the output switching on.
S	Source terminal. May be an input or an	$t_{OFF}$	Delay between applying the digital control
	output.	V <sub>INI.</sub>	input and the output switching off.  Maximum input voltage for logic "0."
D	Drain terminal. May be an input or an	V <sub>INH</sub>	Minimum input voltage for logic "1."
	output.	$I_{INL}$ $(I_{INH})$	Input current of the digital input.
IN	Logic control input.	Charge Injection	A measure of the glitch impulse transferred
$R_{ON}$	Ohmic resistance between D and S.		from the digital input to the analog output
$I_{S}(OFF)$	Source leakage current with the switch		during switching.
	"OFF."	Off Isolation	A measure of unwanted signal coupling
$I_D$ (OFF)	Drain leakage current with the switch		through an "OFF" channel.
	"OFF."	$I_{\mathrm{DD}}$	Positive supply current.
$I_D, I_S (ON)$	Channel leakage current with the switch	$I_{SS}$	Negative supply current.
	"ON."	$I_L$	Logic supply current.

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<sup>&</sup>lt;sup>2</sup>Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

# **Typical Performance Characteristics—ADG417**

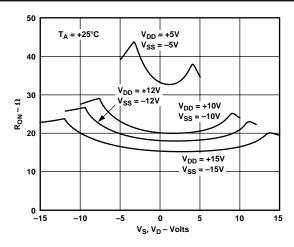


Figure 1.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Dual Supply Voltage

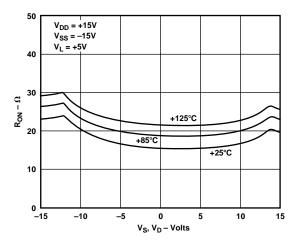


Figure 2.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures

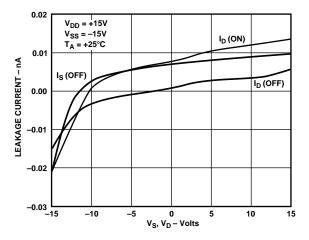


Figure 3. Leakage Currents as a Function of  $V_S(V_D)$ 

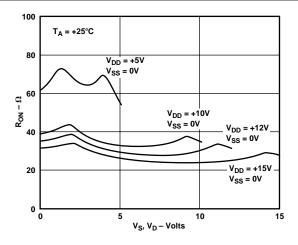


Figure 4.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ): Single Supply Voltage

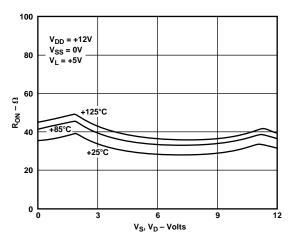


Figure 5.  $R_{ON}$  as a Function of  $V_D$  ( $V_S$ ) for Different Temperatures

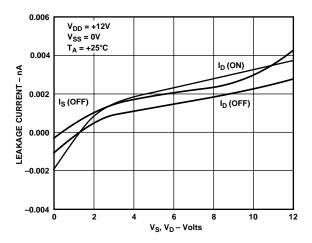


Figure 6. Leakage Currents as a Function of  $V_S$  ( $V_D$ )

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## **ADG417**

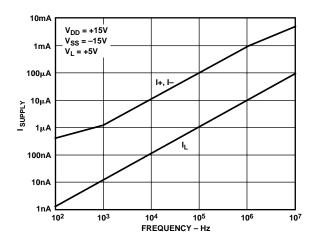


Figure 7. Supply Current vs. Input Switching Frequency

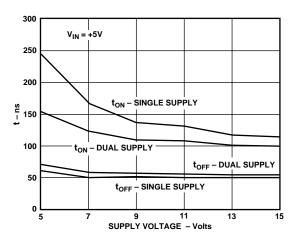
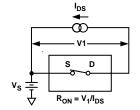


Figure 8. Switching Time vs. Power Supply

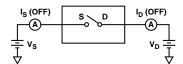
REV. A

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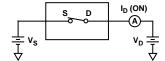
# **Test Circuits**



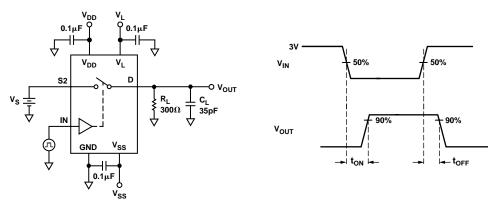
Test Circuit 1. On Resistance



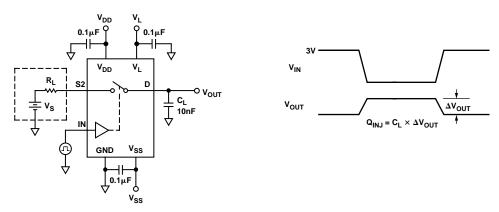
Test Circuit 2. Off Leakage



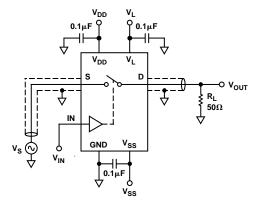
Test Circuit 3. On Leakage



Test Circuit 4. Switching Times



Test Circuit 5. Charge Injection

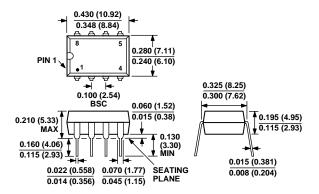


Test Circuit 6. Off Isolation

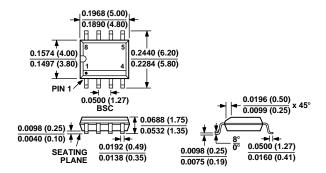
### **OUTLINE DIMENSIONS**

Dimensions shown in inches and (mm).

### 8-Lead Plastic DIP (N-8)



### 8-Lead SOIC (SO-8) (Narrow Body)



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